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Kind regards,

Team Nexperia



# 30 V, 2 A PNP low VCEsat (BISS) transistor Rev. 2 — 4 June 2012

Product data sheet

#### **Product profile** 1.

### 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4230T.

### 1.2 Features and benefits

- Low collector-emiter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>

### 1.3 Applications

Quick reference data

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting

### 1.4 Quick reference data

- Higher efficiency leading to less heat generation
- AEC-Q101 qualified
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

	Quion reference duta					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-2	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-3	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	160	220	Ω



Table 1.

#### 30 V, 2 A PNP low VCEsat (BISS) transistor

### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	E	emitter		3
3	С	collector		
			SOT23 (TO-236AB)	2 sym013

### 3. Ordering information

Table 3. Orde	ering information		
Type number	Package		
	Name	Description	Version
PBSS5230T	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

### 4. Marking

#### Table 4.Marking codes

Type number	Marking code <sup>[1]</sup>
PBSS5230T	%3G

[1] % = placeholder for manufacturing site code

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-2	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-3	А
Ι <sub>Β</sub>	base current			-	-300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

PBSS5230T Product data sheet

30 V, 2 A PNP low VCEsat (BISS) transistor

### 6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	<u>[1]</u>	-	-	417	K/W
	from junction to ambient		[2]	-	-	260	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

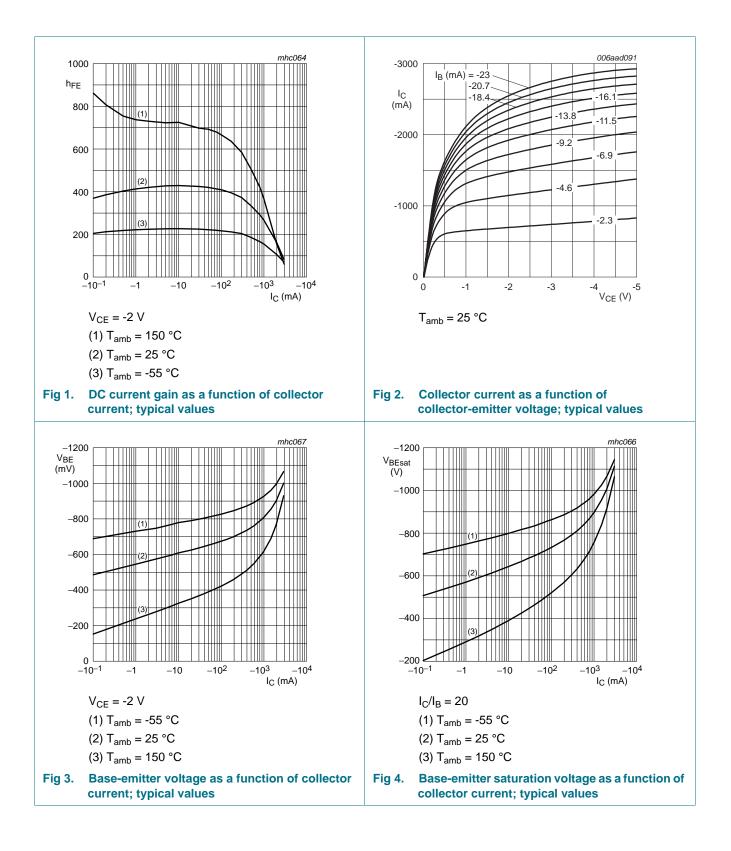
### 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	$V_{CB}$ = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	300	450	-	
			200	290	-	
		$    V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}; \text{ pulsed};                                    $	100	180	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; $T_{amb}$ = 25 °C	-	-70	-110	mV
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; $T_{amb}$ = 25 °C	-	-140	-225	mV
		$I_{C} = -2 \text{ A}; I_{B} = -200 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-240	-350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	160	220	Ω
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -2 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	-	-	-0.75	V
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	200	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	23	28	pF

### **NXP Semiconductors**

# PBSS5230T

### 30 V, 2 A PNP low VCEsat (BISS) transistor

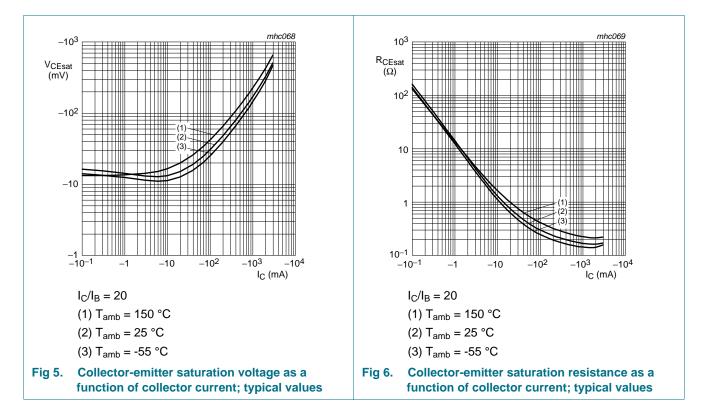


PBSS5230T

### **NXP Semiconductors**

# **PBSS5230T**

#### 30 V, 2 A PNP low VCEsat (BISS) transistor

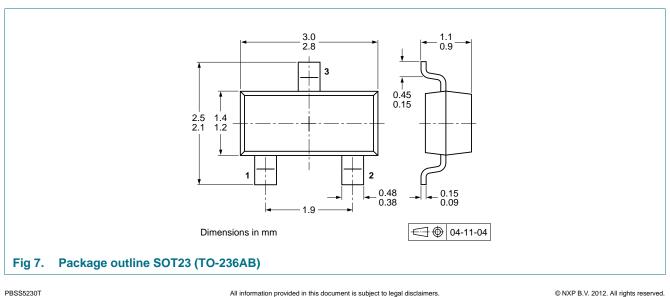


#### **Test information** 8.

#### 8.1 **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

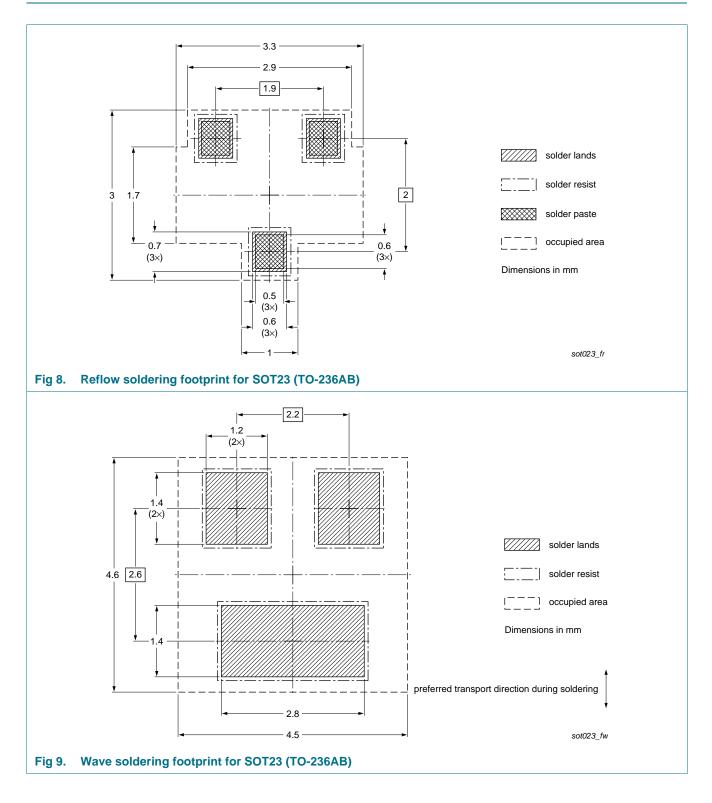
#### **Package outline** 9.



**Product data sheet** 

#### 30 V, 2 A PNP low VCEsat (BISS) transistor

### 10. Soldering



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### 30 V, 2 A PNP low VCEsat (BISS) transistor

### 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5230T v.2	20120604	Product data sheet	-	PBSS5230T v.1		
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>					
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
	<ul> <li><u>1 "Product profile"</u>: updated</li> </ul>					
	• 4 "Marking": corrected					
	• Table 5.: updated					
	<ul> <li>7 "Characteristics": V<sub>CEsat</sub> corrected, Fig 1. to Fig 6. added</li> </ul>					
	8 "Test information": added					
	<ul> <li>9 "Package outline": replaced by minimized package outline drawing</li> </ul>					
	<ul> <li>10 "Soldering": added</li> </ul>					
PBSS5230T v.1	20031218	Product data sheet	-	-		

#### 30 V, 2 A PNP low VCEsat (BISS) transistor

### 12. Legal information

### 12.1 Data sheet status

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions'

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Product data sheet

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### 30 V, 2 A PNP low VCEsat (BISS) transistor

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